

Chiharu Ota

List of Publications by Year in descending order

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Version: 2024-02-01

12
papers

131
citations

1651377

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1762888

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12
all docs

12
docs citations

12
times ranked

41
citing authors

#	ARTICLE	IF	CITATIONS
1	Structural study of single Shockley stacking faults terminated near substrate/epilayer interface in 4H-SiC. Japanese Journal of Applied Physics, 2022, 61, SC1005.	0.8	8
2	Conversion of Shockley partial dislocation pairs from unexpandable to expandable combinations after epitaxial growth of 4H-SiC. Journal of Applied Physics, 2021, 130, .	1.1	6
3	Origin and Generation Process of a Triangular Single Shockley Stacking Fault Expanding from the Surface Side in 4H-SiC PIN Diodes. Journal of Electronic Materials, 2021, 50, 6504-6511.	1.0	13
4	Single Shockley stacking fault expansion from immobile basal plane dislocations in 4H-SiC. Japanese Journal of Applied Physics, 2021, 60, SBBD01.	0.8	10
5	Informative Aspects of Molten KOH Etch Pits Formed at Basal Plane Dislocations on the Surface of 4H-SiC. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 2000332.	0.8	7
6	Direct confirmation of structural differences in single Shockley stacking faults expanding from different origins in 4H-SiC PIN diodes. Journal of Applied Physics, 2020, 128, .	1.1	13
7	Triangular Single Shockley Stacking Fault Analyses on 4H-SiC PIN Diode with Forward Voltage Degradation. Journal of Electronic Materials, 2020, 49, 5232-5239.	1.0	12
8	Dependences of contraction/expansion of stacking faults on temperature and current density in 4H-SiC p-n diodes. Japanese Journal of Applied Physics, 2018, 57, 061301.	0.8	27
9	V&F; Degradation of 4H-SiC PIN Diodes Using Low-BPD Wafers. Materials Science Forum, 0, 778-780, 851-854.	0.3	10
10	Initiation of Shockley Stacking Fault Expansion in 4H-SiC P-i-N Diodes. Materials Science Forum, 0, 963, 280-283.	0.3	7
11	Photoluminescence Analysis of Individual Partial Dislocations in 4H-SiC Epilayers. Materials Science Forum, 0, 1004, 376-386.	0.3	13
12	Transmission Electron Microscopy Study of Single Shockley Stacking Faults in 4H-SiC Expanded from Basal Plane Dislocation Segments Accompanied by Threading Edge Dislocations on both Ends. Materials Science Forum, 0, 1062, 258-262.	0.3	5